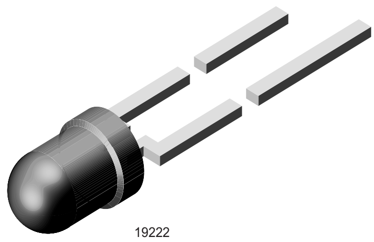
High Efficiency Blue LED, ∅ 3 mm Tinted Non-Diffused Package

Description

This device has been redesigned in 1998 replacing SiC by GaN technology to meet the increasing demand for high efficiency blue LEDs.

It is housed in a 3 mm tinted non-diffused plastic package.

All packing units are categorized in luminous intensity groups. That allows users to assemble LEDs with uniform appearance.



19222

e2

Pb

Pb-free

Features

- GaN on SiC technology
- Standard ∅ 3 mm (T-1) package
- Small mechanical tolerances
- Medium viewing angle
- Very high intensity
- Luminous intensity categorized
- ESD class 1
- Lead-free device

Applications

Status lights
OFF / ON indicator
Background illumination
Readout lights
Maintenance lights
Legend light

Parts Table

Part	Color, Luminous Intensity	Angle of Half Intensity (±φ)	Technology
TLHB4200	Blue, I_V > 25 mcd	22 °	GaN on SiC
TLHB4201	Blue, I_V = (40 to 132) mcd	22 °	GaN on SiC

Absolute Maximum Ratings

T_{amb} = 25 °C, unless otherwise specified
TLHB420.

Parameter	Test condition	Symbol	Value	Unit
Reverse voltage		V_R	5	V
DC Forward current	$T_{amb} \le 60$ °C	I_F	20	mA
Surge forward current	$t_p \le 10$ µs	I_{FSM}	0.1	A
Power dissipation	$T_{amb} \le 60$ °C	P_V	100	mW
Junction temperature		T_j	100	°C
Operating temperature range		T_{amb}	- 40 to + 100	°C
Storage temperature range		T_{stg}	- 40 to + 100	°C
Soldering temperature	t ≤ 5 s, 2 mm from body	T_{sd}	260	°C
Thermal resistance junction/ ambient		R_{thJA}	400	K/W

Optical and Electrical Characteristics

T_{amb} = 25 °C, unless otherwise specified

Blue

Parameter	Test condition	Part	Symbol	Min	Typ.	Max	Unit
Luminous intensity [1]	I_F = 20 mA	TLHB4200	I_V	25	50		mcd
		TLHB4201	I_V	40		132	mcd
Dominant wavelength	I_F = 10 mA		λ_d		466		nm
Peak wavelength	I_F = 10 mA		λ_p		428		nm
Angle of half intensity	I_F = 10 mA		φ		± 22		deg
Forward voltage	I_F = 20 mA		V_F		3.9	4.5	V
Reverse voltage	I_R = 10 µA		V_R	5			V

[1] in one Packing Unit $I_{Vmin}/I_{Vmax} \leq 0.5$

Typical Characteristics (T_{amb} = 25 °C unless otherwise specified)

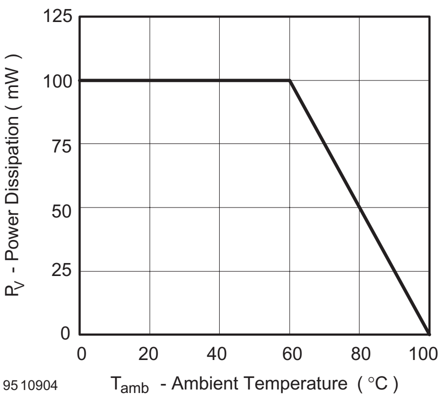


Figure 1. Power Dissipation vs. Ambient Temperature

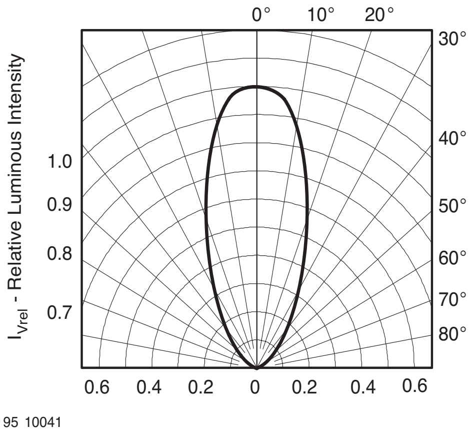


Figure 3. Rel. Luminous Intensity vs. Angular Displacement

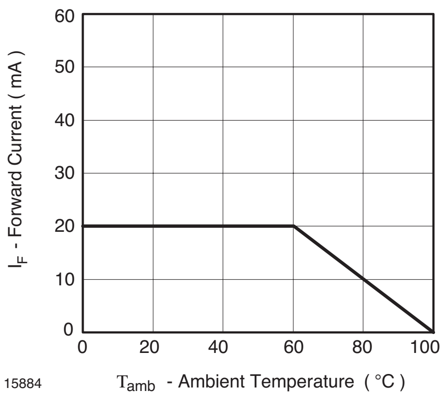


Figure 2. Forward Current vs. Ambient Temperature for InGaN

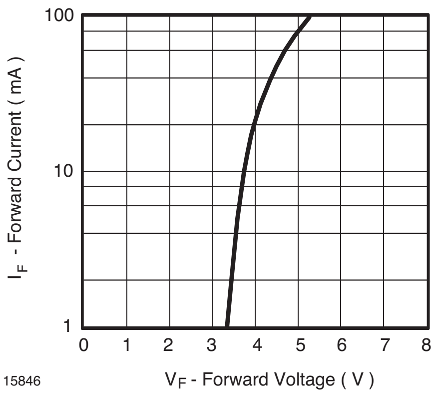


Figure 4. Forward Current vs. Forward Voltage

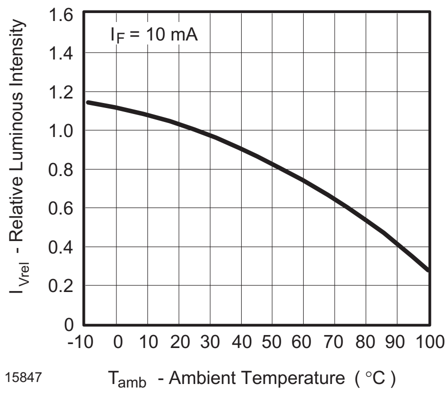


Figure 5. Rel. Luminous Flux vs. Ambient Temperature

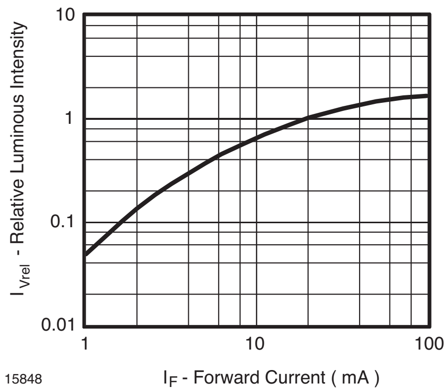


Figure 6. Relative Luminous Flux vs. Forward Current

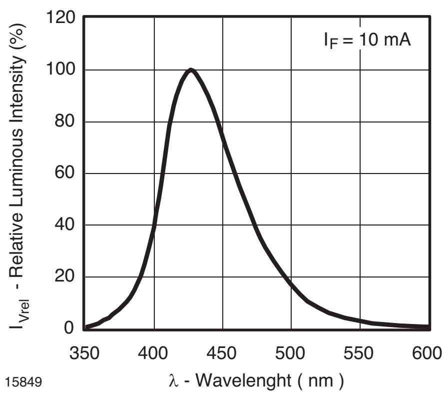
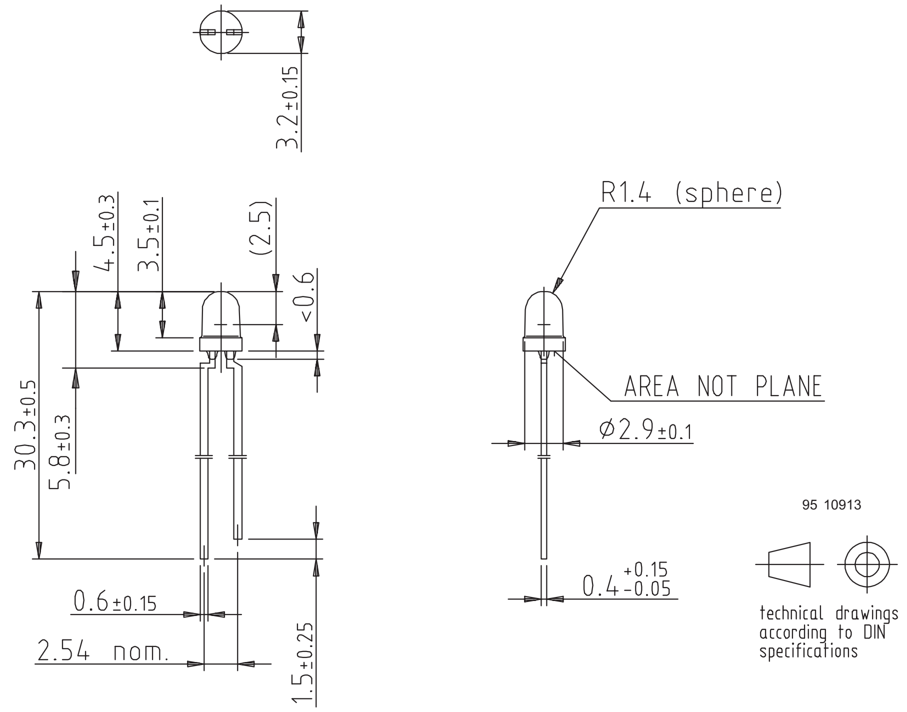


Figure 7. Relative Intensity vs. Wavelength

Package Dimensions in mm



Ozone Depleting Substances Policy Statement

It is the policy of **Vishay Semiconductor GmbH** to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operatingsystems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

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